

N-channel 620 V, 0.95  $\Omega$  typ., 7.0 A Power MOSFET in  
I<sup>2</sup>PAKFP and TO-220

Datasheet - production data

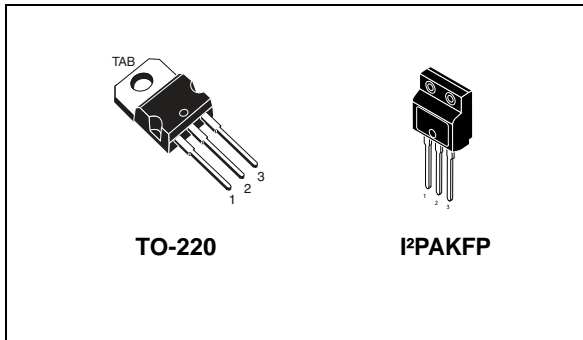
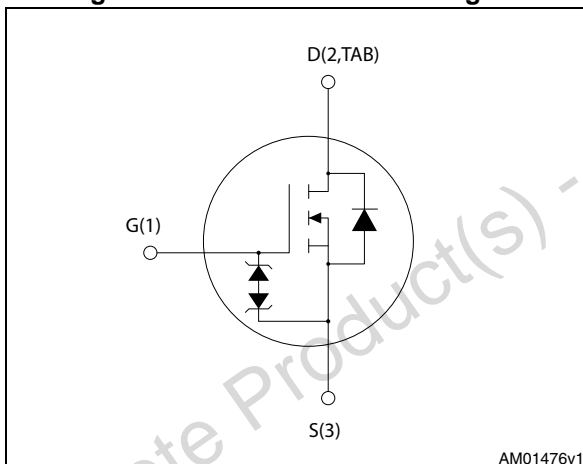


Figure 1. Internal schematic diagram



## Features

Order codes	V <sub>DSS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STFILED627	620 V	< 1.2 $\Omega$	7.0 A	30 W
STPLED627				

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

## Applications

- LED lighting applications

## Description

These Power MOSFETs boast extremely low on-resistance and very good dv/dt capability, rendering them suitable for buck-boost and flyback topologies.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STFILED627	LED627	I <sup>2</sup> PAKFP	Tube
STPLED627		TO-220	

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Revision history</b> .....	<b>14</b>

Obsolete Product(s) - Obsolete Product(s)



# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		I <sup>2</sup> PAKFP	TO-220	
V <sub>DS</sub>	Drain-source voltage	620		V
V <sub>GS</sub>	Gate-source voltage	± 30		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	7.0 <sup>(1)</sup>		A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	4.0 <sup>(1)</sup>		A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	22 <sup>(1)</sup>		A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	30	90	W
I <sub>AR</sub> <sup>(3)</sup>	Avalanche current, repetitive or not-repetitive	5.5		A
E <sub>AS</sub> <sup>(4)</sup>	Single pulse avalanche energy	140		mJ
ESD	Gate-source human body model (R = 1.5 kΩ, C = 100 pF)	2.5		kV
dv/dt <sup>(5)</sup>	Peak diode recovery voltage slope	12		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)	2500		V
T <sub>stg</sub>	Storage temperature	-55 to 150		°C
T <sub>j</sub>	Max. operating junction temperature	150		°C

- Limited by maximum junction temperature.
- Pulse width limited by safe operating area.
- Pulse width limited by T<sub>j</sub> max.
- Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = I<sub>AR</sub>, V<sub>DD</sub> = 50 V.
- I<sub>SD</sub> ≤ 5.5 A, di/dt ≤ 400 A/μs, V<sub>DD</sub> = 80% V<sub>(BR)DSS</sub>, V<sub>DSpeak</sub> ≤ V<sub>(BR)DSS</sub>.

**Table 3. Thermal data**

Symbol	Parameter	I <sup>2</sup> PAKFP	TO-220	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max.	4.17	1.39	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max.	62.5		°C/W

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	620			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 620\text{ V}$ $V_{DS} = 620\text{ V}$ , $T_C = 125\text{ °C}$			0.8 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 9$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.6	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2.8\text{ A}$		0.95	1.2	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	890 110 18	-	pF
$C_{oss}$	Output capacitance		-	110	-	pF
$C_{riss}$	Reverse transfer capacitance		-	18	-	pF
$C_{oss(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }480\text{ V}$	-	28	-	pF
$C_{oss(tr)}^{(2)}$	Equivalent output capacitance time related		-	63	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	3.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 496\text{ V}$ , $I_D = 5.5\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> )	-	35	-	nC
$Q_{gs}$	Gate-source charge		-	4.5	-	nC
$Q_{gd}$	Gate-drain charge		-	23	-	nC

1. It is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .
2. It is defined as a constant equivalent capacitance giving the same storage energy as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 310 \text{ V}$ , $I_D = 2.75 \text{ A}$ , $R_G = 4.7 \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 17</a> )	-	22	-	ns
$t_r$	Rise time		-	12	-	ns
$t_{d(off)}$	Turn-off-delay time		-	49	-	ns
$t_f$	Fall time		-	20	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		5.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		27	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5.5 \text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 5.5 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 22</a> )	-	290		ns
$Q_{rr}$	Reverse recovery charge		1.9		$\mu\text{C}$	
$I_{RRM}$	Reverse recovery current		13.5		A	
$t_{rr}$	Reverse recovery time	$I_{SD} = 5.5 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 22</a> )	-	335		ns
$Q_{rr}$	Reverse recovery charge		2.4		$\mu\text{C}$	
$I_{RRM}$	Reverse recovery current		14.5		A	

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage ( $I_D = 0$ )	$I_{gs} = \pm 1 \text{ mA}$	30	-		V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

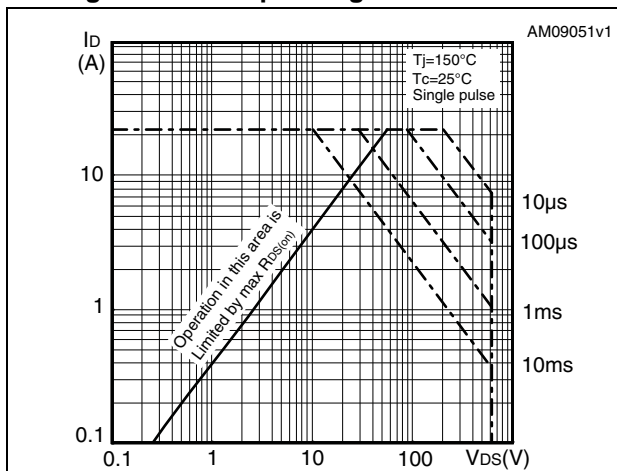


Figure 3. Thermal impedance for TO-220

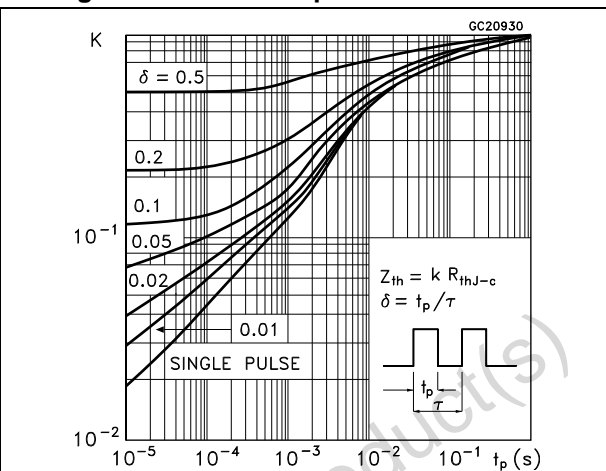


Figure 4. Safe operating area for I<sup>2</sup>PAKFP

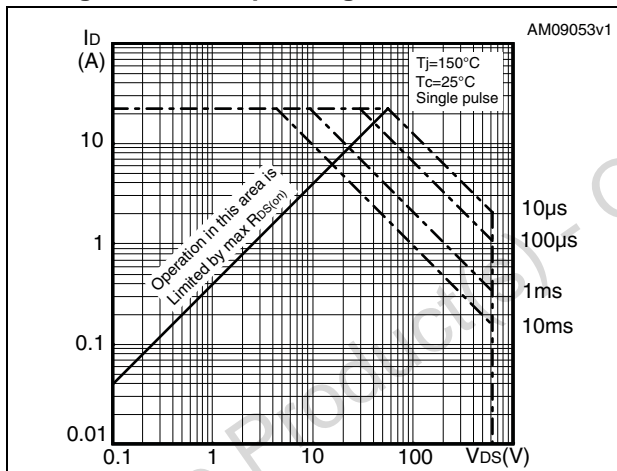


Figure 5. Thermal impedance for I<sup>2</sup>PAKFP

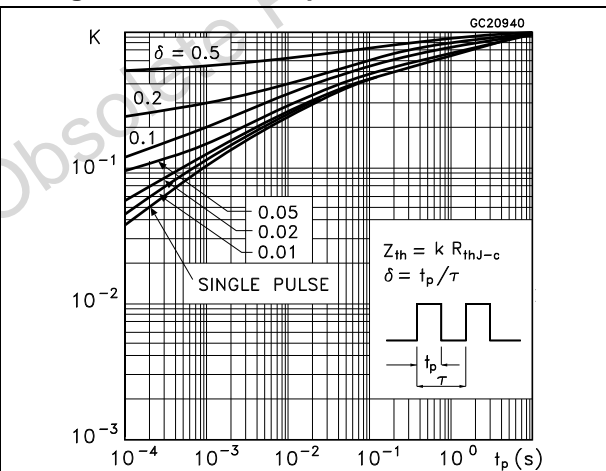


Figure 6. Output characteristics

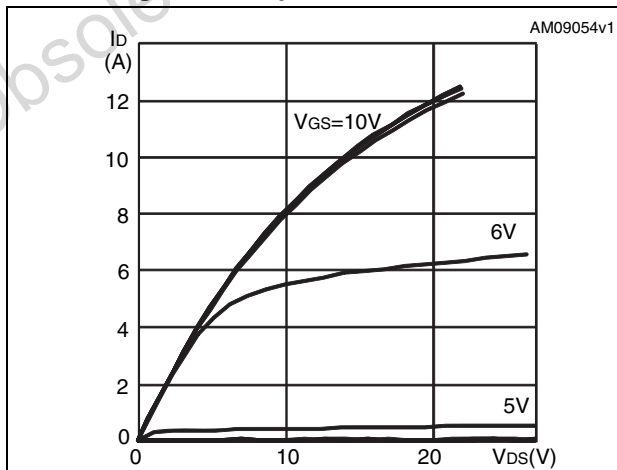


Figure 7. Transfer characteristics

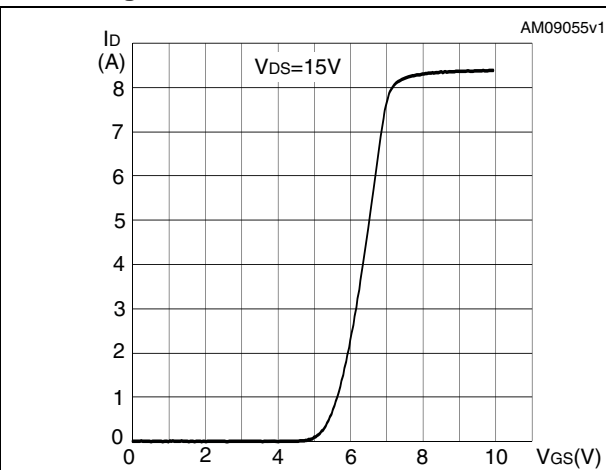


Figure 8. Gate charge vs gate-source voltage

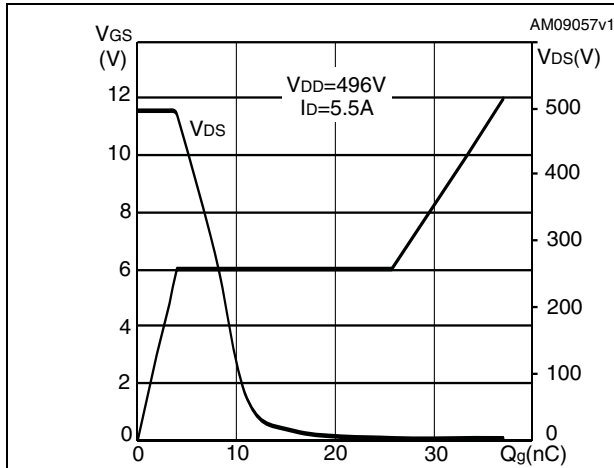


Figure 9. Static drain-source on-resistance

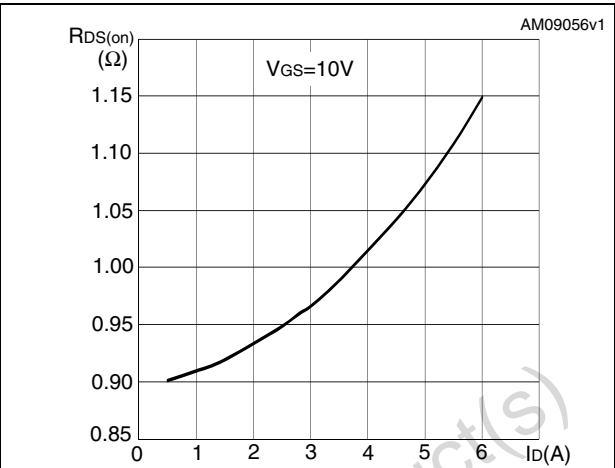


Figure 10. Capacitance variations

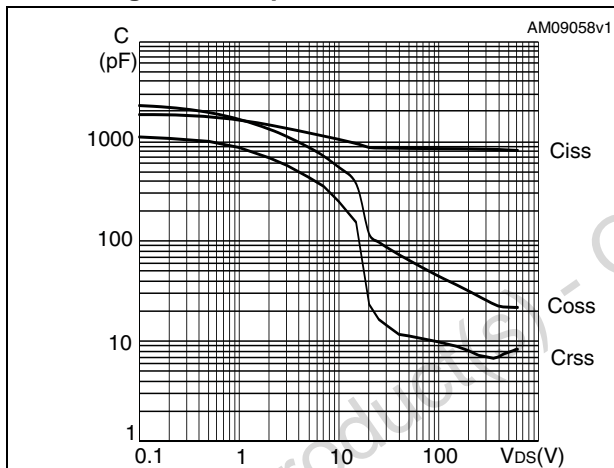


Figure 11. Output capacitance stored energy

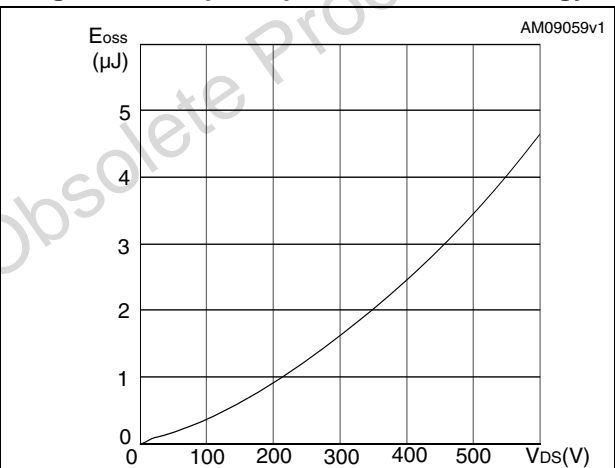


Figure 12. Normalized gate threshold voltage vs temperature

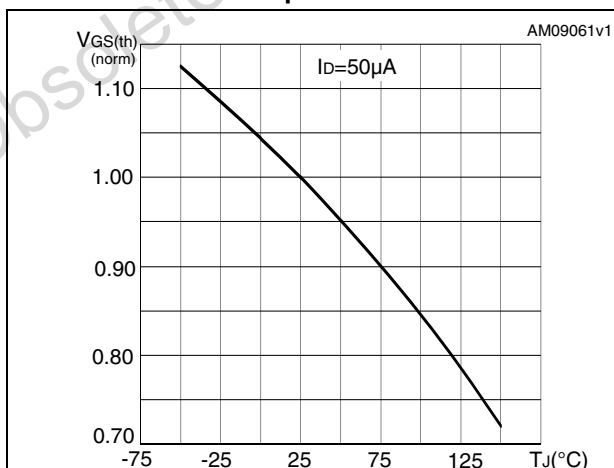


Figure 13. Normalized on-resistance vs temperature

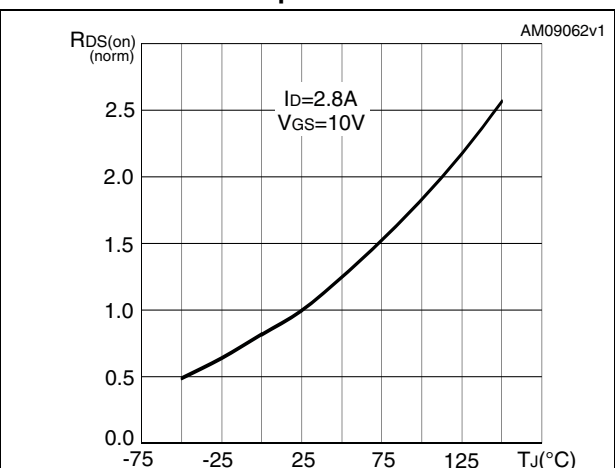


Figure 14. Normalized  $B_{VDSS}$  vs temperature

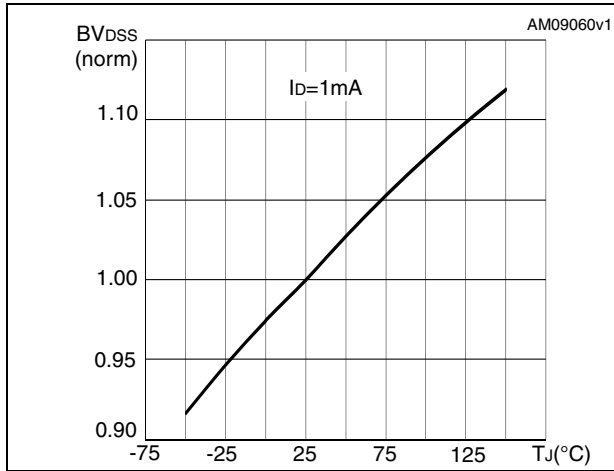


Figure 15. Source-drain diode forward characteristics

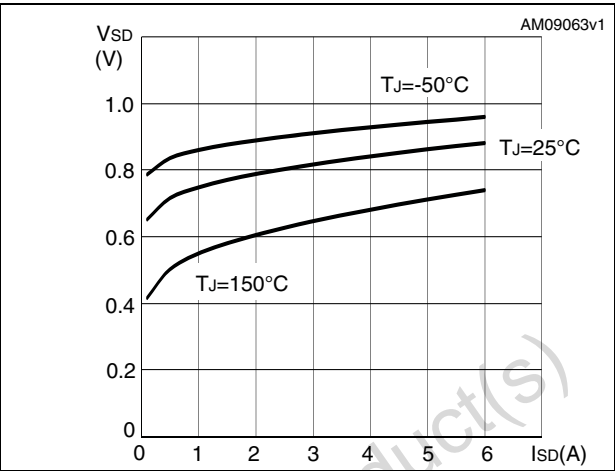
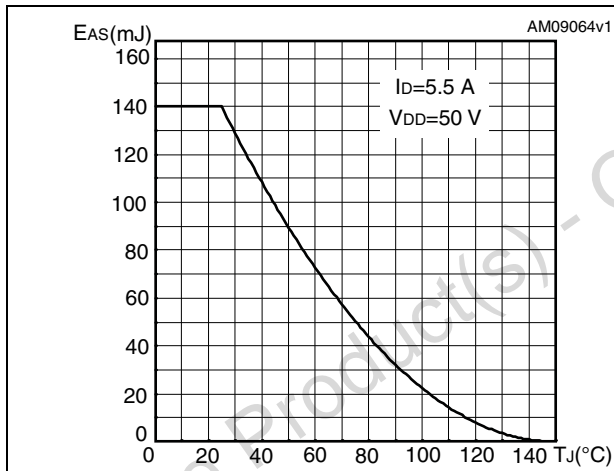


Figure 16. Maximum avalanche energy vs temperature





### 3 Test circuits

Figure 17. Switching times test circuit for resistive load

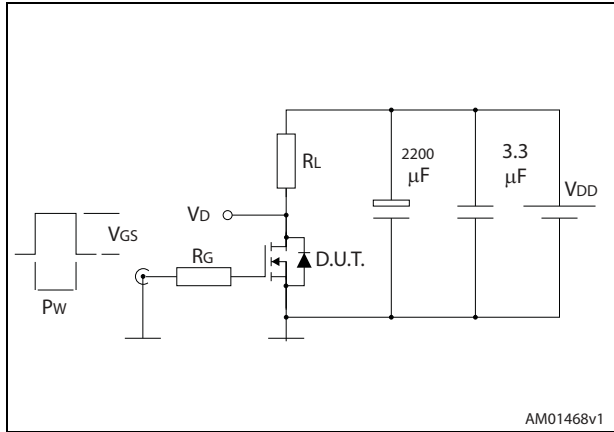


Figure 18. Gate charge test circuit

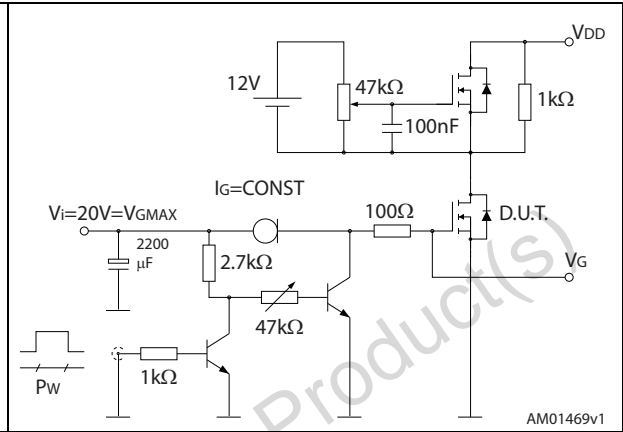


Figure 19. Test circuit for inductive load switching and diode recovery times

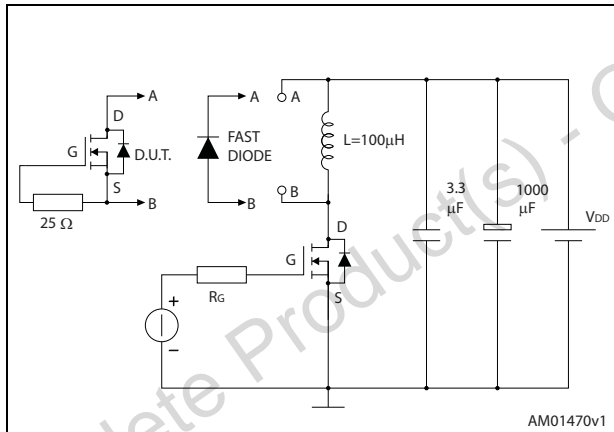


Figure 20. Unclamped Inductive load test circuit

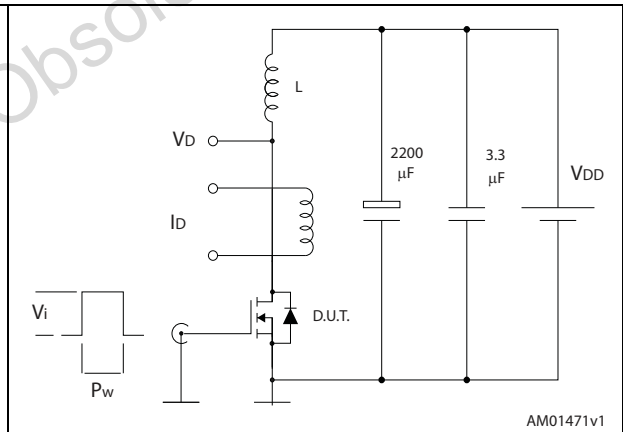


Figure 21. Unclamped inductive waveform

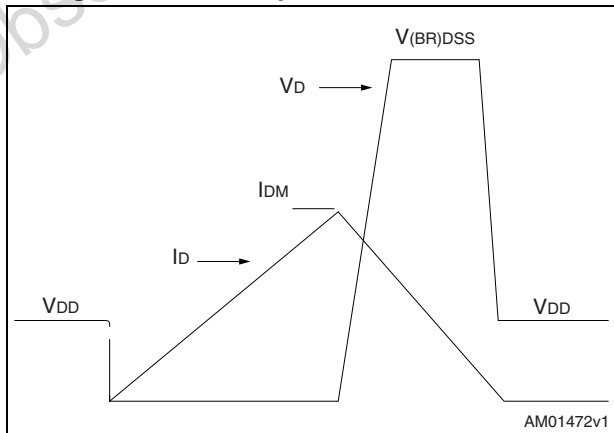
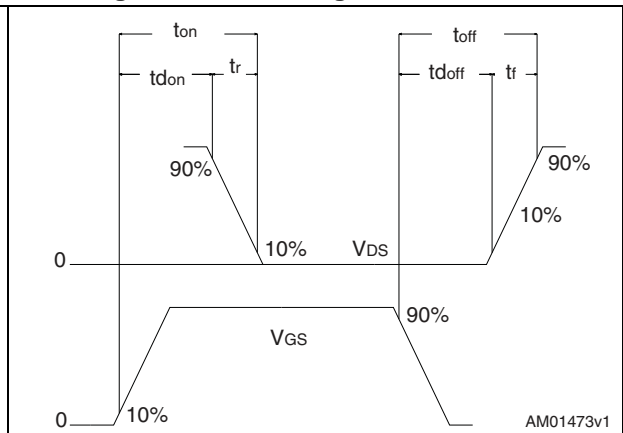


Figure 22. Switching time waveform



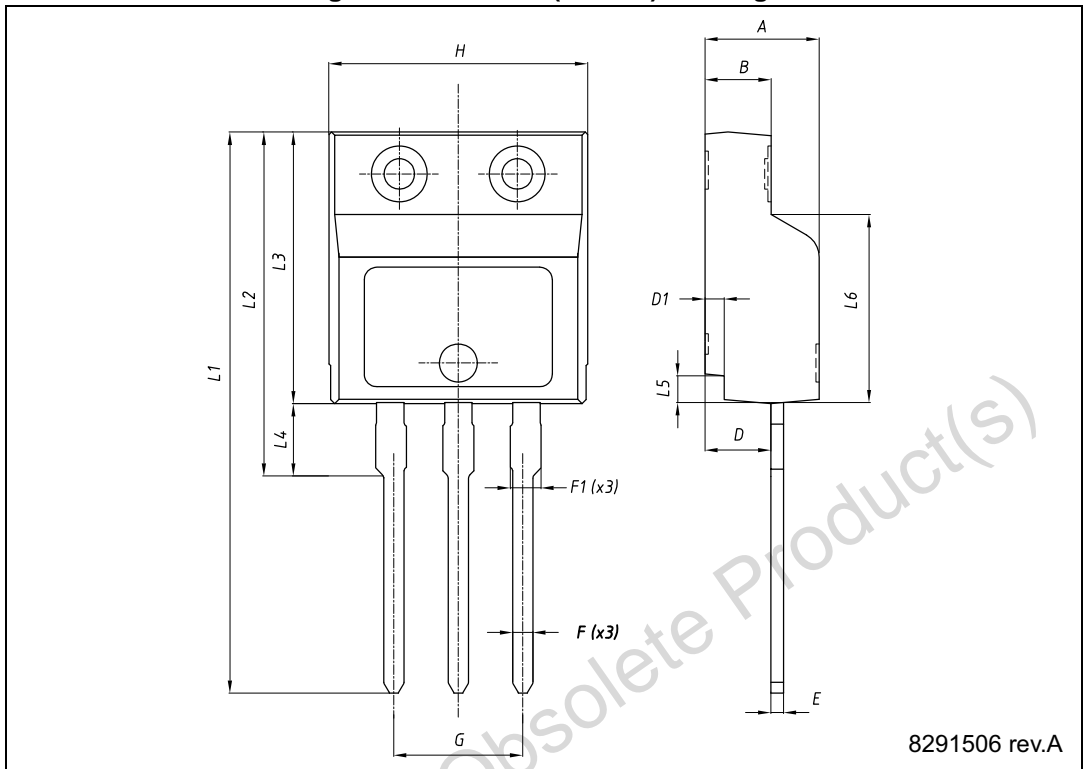
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 9. I<sup>2</sup>PAKFP (TO-281) mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

Figure 23. I<sup>2</sup>PAKFP (TO-281) drawings

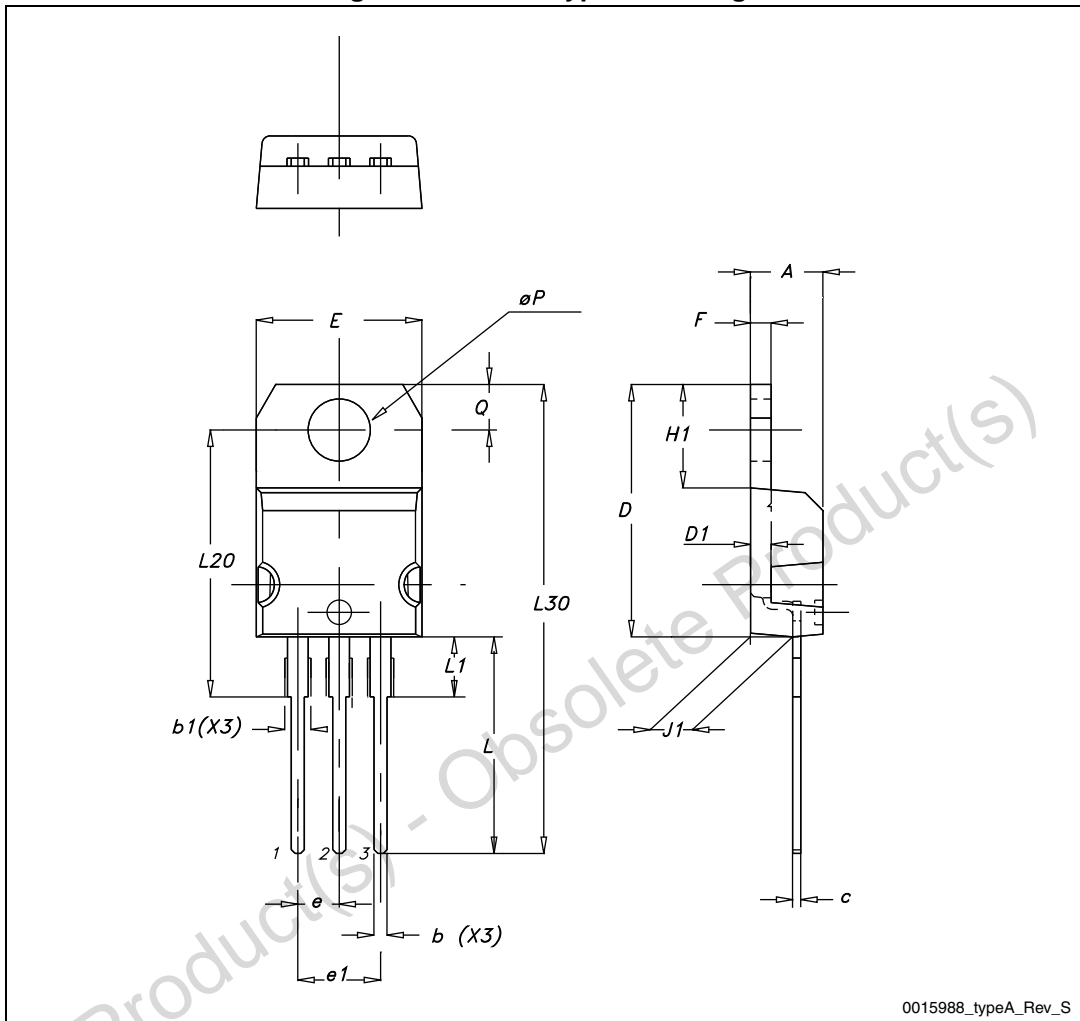


8291506 rev.A

Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 24. TO-220 type A drawings



0015988\_typeA\_Rev\_S

## 5 Revision history

Table 11. Document revision history

Date	Revision	Changes
28-Aug-2013	1	First release.

Obsolete Product(s) - Obsolete Product(s)

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